

| | | | | | | |
|-----|-------|---|---|----|-----|------------------|
| S62 | 14608 | ((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/02 21:44 |
| S63 | 5 | S62 and (((gate near2 (dielectric or insulat\$3)) near5 (anneal\$3 or heat\$3)) same (vacuum or (below near2 ("atm" or atmospheric) near2 pressure)))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/02 21:51 |
| S64 | 9677 | ((438/149) or (438/151) or (438/164) or (438/166) or (438/479) or (438/482) or (438/485) or (438/486) or (438/487) or (438/488) or (438/491) or (438/758) or (438/778) or (438/787)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/12/16 17:57 |
| S65 | 101 | S64 and (vacuum near10 (("SiO" or (silicon adj oxide)) or (gate adj (insulat\$3 or passivat\$3 or dielectric)))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/16 18:06 |
| S66 | 43 | S64 and (vacuum near10 (("SiO" or (silicon adj oxide)) or (gate adj (insulat\$3 or passivat\$3 or dielectric))) near10 deposit\$3) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/16 18:07 |
| S67 | 3 | S64 and (vacuum near10 (("SiO" or (silicon adj oxide)) or (gate adj (insulat\$3 or passivat\$3 or dielectric))) near10 deposit\$3 near10 (anneal\$3 or heat\$3)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/16 18:08 |
| S68 | 106 | (vacuum near10 (("SiO" or (silicon adj oxide)) or (gate adj (insulat\$3 or passivat\$3 or dielectric))) near10 deposit\$3 near10 (anneal\$3 or heat\$3)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/16 18:26 |

| | | | | | | |
|-----|------|--|---|----|-----|------------------|
| S69 | 101 | deposit\$3 near10 vacuum near10 (anneal\$3 or heat\$3) near10 ("SiO" or (silicon adj oxide)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/16 18:28 |
| S70 | 15 | S69 not S68 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/16 18:29 |
| S71 | 1297 | (438/151).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/12/19 14:48 |
| S72 | 902 | (438/758).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/12/19 16:30 |
| S73 | 1387 | (438/778).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/12/19 18:36 |
| S74 | 817 | (438/787).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/12/19 17:51 |
| S75 | 1109 | (438/488).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/12/19 15:33 |
| S76 | 1062 | (438/166).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/12/19 19:06 |

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|---|---|------------------|---------|------------------|
| L1 | 1548 | (438/149).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/12/19 19:09 |
| S1 | 12368 | ((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/02 21:44 |
| S2 | 0 | ((gate near3 insulat\$4) same (anneal\$3 or heat\$3)) near5 vacuum | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 19:15 |
| S3 | 0 | ((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:15 |
| S4 | 0 | ((sio or (silicon near2 oxide)) and (anneal\$3 or heat\$3)) near5 vacuum | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/15 22:01 |
| S5 | 12368 | ((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/07/16 14:13 |
| S6 | 112 | ((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:17 |

| | | | | | | |
|-----|--------|--|---|----|----|------------------|
| S7 | 6 | ((gate near3 insulat\$4) same (anneal\$3 or heat\$3)) near5 vacuum | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:15 |
| S8 | 5 | ((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS:) and (((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:19 |
| S9 | 1353 | (poly near2 crystall\$8) same (poly near2 silicon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 16:32 |
| S10 | 455320 | tft or (thin near2 film) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:21 |
| S11 | 275 | ((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/14 17:49 |
| S12 | 291495 | (anneal\$3 or heat\$3) same (vacuum or (low near2 pressure)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:29 |
| S13 | 275 | ((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:38 |
| S14 | 54 | ((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))) and ((anneal\$3 or heat\$3) same (vacuum or (low near2 pressure))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:24 |

| | | | | | | |
|-----|--------|--|---|----|----|------------------|
| S15 | 249811 | (anneal\$3 or heat\$3) same (vacuum) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:36 |
| S16 | 27 | ((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))) and ((anneal\$3 or heat\$3) same (vacuum)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:30 |
| S17 | 58093 | (anneal\$3 or heat\$3) near3 (vacuum) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:39 |
| S18 | 10 | ((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))) and ((anneal\$3 or heat\$3) near3 (vacuum)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:37 |
| S19 | 605 | ((poly near2 crystall\$8) same (poly near2 silicon)) and (tft or (thin near2 film)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:38 |
| S20 | 5134 | ((anneal\$3 or heat\$3) near3 (vacuum)) same insulat\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:50 |
| S21 | 2991 | ((anneal\$3 or heat\$3) near3 (vacuum)) near5 insulat\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:51 |
| S22 | 1 | ((anneal\$3 or heat\$3) near3 (vacuum)) near5 insulat\$3) and ((poly near2 crystall\$8) same (poly near2 silicon)) and (tft or (thin near2 film))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:50 |
| S23 | 9 | ((anneal\$3 or heat\$3) near3 (vacuum)) near5 (gate near3 insulat\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 14:51 |
| S24 | 3613 | (anneal\$3 or heat\$3) near4 (insulat\$3 or (gate near2 insulat\$3)) near4 vacuum | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 16:32 |

| | | | | | | |
|-----|--------|--|---|----|-----|------------------|
| S25 | 1353 | (poly near2 crystall\$8) same (poly near2 silicon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 16:32 |
| S26 | 2 | ((anneal\$3 or heat\$3) near4 (insulat\$3 or (gate near2 insulat\$3)) near4 vacuum) and ((poly near2 crystall\$8) same (poly near2 silicon)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/16 16:33 |
| S27 | 12423 | ((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/07/27 19:15 |
| S28 | 2538 | ((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/28 23:20 |
| S29 | 412 | ((((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 19:17 |
| S30 | 124905 | vacuum near5 chamber | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 19:18 |
| S31 | 12653 | fns or ((fowler adj Nordheim) near2 stress) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/28 23:17 |

| | | | | | | |
|-----|-----|--|---|----|----|------------------|
| S32 | 69 | (((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (vacuum near5 chamber) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 19:19 |
| S33 | 1 | (((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (vacuum near5 chamber)) and (fns or ((fowler adj Nordheim) near2 stress)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 19:19 |
| S34 | 3 | (((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (fns or ((fowler adj Nordheim) near2 stress)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 19:20 |
| S35 | 212 | (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (vacuum near5 chamber) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 15:15 |

| | | | | | | |
|-----|--------|--|---|----|-----|------------------|
| S36 | 3 | (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (vacuum near5 chamber)) and (fns or ((fowler adj Nordheim) near2 stress)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 19:21 |
| S37 | 0 | "6638876".URPN. | USPAT | OR | OFF | 2004/07/27 19:23 |
| S38 | 24 | ("4585492" "5210056" "5578848" "5880040" "6020024" "6121130" "6136725" "6165834" "6168980" "6177363" "6191011" "6258690" "6274454" "6287897" "6291867" "6300203" "6306742" "6326231" "6326258" "6333557" "6335049" "6337289" "6338996" "6451713").PN. | USPAT | OR | OFF | 2004/07/27 19:23 |
| S39 | 3 | (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and (((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS:) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 19:25 |
| S40 | 4 | (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and vacuum | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 19:26 |
| S41 | 39 | (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 20:08 |
| S42 | 211701 | sio or (silicon near2 oxide) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 20:08 |
| S43 | 29 | (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and (sio or (silicon near2 oxide)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 20:08 |

| | | | | | | |
|-----|-------|--|---|----|----|------------------|
| S44 | 529 | ((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 20:24 |
| S45 | 50 | (fns or ((fowler adj Nordheim)) near2 stress | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 20:25 |
| S46 | 1 | ((((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and vacuum) and (fns or ((fowler adj Nordheim) near2 stress)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 20:26 |
| S47 | 13 | ((((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 20:30 |
| S48 | 132 | ((((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and vacuum | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/27 20:40 |
| S49 | 12653 | fns or ((fowler adj Nordheim) near2 stress) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/28 23:17 |
| S50 | 2538 | ((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/28 23:20 |
| S51 | 4 | (fns or ((fowler adj Nordheim) near2 stress)) same (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/28 23:21 |
| S52 | 0 | (fns or ((fowler adj Nordheim) near2 stress)) near5 (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/28 23:21 |
| S53 | 2 | (fns or ((fowler adj Nordheim) near2 stress)) near10 (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/07/28 23:21 |

| | | | | | | |
|-----|-------|---|---|----|-----|------------------|
| S54 | 13414 | ((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/01/14 17:48 |
| S55 | 103 | S54 and (anneal\$3 near4 (gate near2 insulat\$3)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/14 17:50 |
| S56 | 44 | S55 and vacuum | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/14 17:50 |
| S57 | 26 | "6168980" | USPAT | OR | OFF | 2005/06/07 13:08 |
| S58 | 1 | ("6168980").PN. | USPAT | OR | OFF | 2005/06/07 13:08 |
| S59 | 14087 | ((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/07 15:14 |
| S60 | 74 | S59 and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (vacuum near5 chamber) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 15:16 |
| S61 | 40 | S60 and ((h2 or hydrogen) near5 atmosphere) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 15:16 |